Jan 2016

SemiHow
Know-How for Semiconductor

HRLE320N03K

30V N-Channel Trench MOSFET

Features

- ❑ Low Dense Cell Design
- ❑ Reliable and Rugged
- ❑ Advanced Trench Process Technology

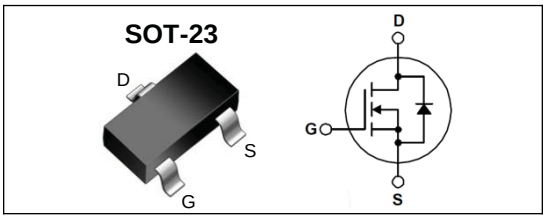
Key Parameters

Parameter	Value	Unit
BV_{DSS}	30	V
I_D	5	A
$R_{DS(on),\ typ\ @10V}$	27	mΩ
$R_{DS(on),\ typ\ @4.5V}$	33	mΩ

Application

- ❑ Power Management in Inverter System
- ❑ Synchronous Rectification

Package & Internal Circuit



Absolute Maximum Ratings

T_A=25℃ unless otherwise specified

Symbol	Parameter		Value	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current	T_A = 25℃	5	A
		T_A = 70℃	4	A
I_{DM}	Pulsed Drain Current		20	A
P_D	Power Dissipation	T_A = 25℃	1.4	W
		T_A = 70℃	0.9	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient (t≤10s)	--	90	℃/W

Electrical Characteristics T_J=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	1.0	--	3.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 5 A	--	27	32	mΩ
		V_{GS} = 4.5 V, I_D = 4 A	--	33	40	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5, I_D = 5 A	--	15	--	S
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 24 V, T_J = 55℃	--	--	5	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	--	--	±100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1.0 MHz	--	450	--	pF
C_{oss}	Output Capacitance		--	62	--	pF
C_{rss}	Reverse Transfer Capacitance		--	50	--	pF
R_g	Gate Resistance	V_{GS} = 0 V, V_{DS} = 0 V, f = 1MHz	--	2.5	--	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 15 V, I_D = 5 A, R_G = 6 Ω	--	15	--	ns
t_r	Turn-On Rise Time		--	9	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	31	--	ns
t_f	Turn-Off Fall Time		--	12	--	ns
$Q_{g(10V)}$	Total Gate Charge	V_{DS} = 15 V, I_D = 5 A, V_{GS} = 10 V	--	8.5	11	nC
$Q_{g(4.5V)}$			--	4.0	5.2	nC
Q_{gs}	Gate-Source Charge		--	1.0	--	nC
Q_{gd}	Gate-Drain Charge		--	1.5	--	nC
Source-Drain Diode Maximum Ratings and Characteristics						
I_S	Continuous Source-Drain Diode Forward Current		--	--	5	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	20	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 3 A, V_{GS} = 0 V	--	--	1.3	V
trr	Reverse Recovery Time	I_S = 5 A, V_{GS} = 0 V, di_F/dt = 100 A/μs	--	10	--	ns
Qrr	Reverse Recovery Charge		--	2.5	--	nC

Typical Characteristics

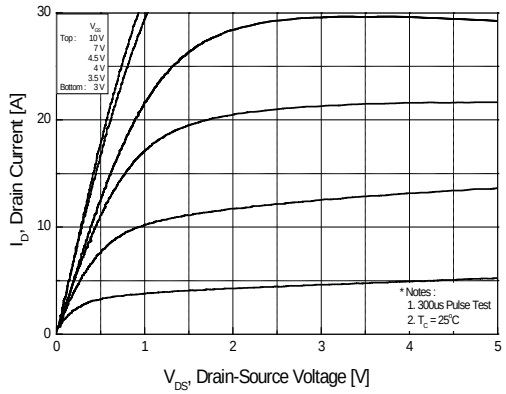


Figure 1. On Region Characteristics

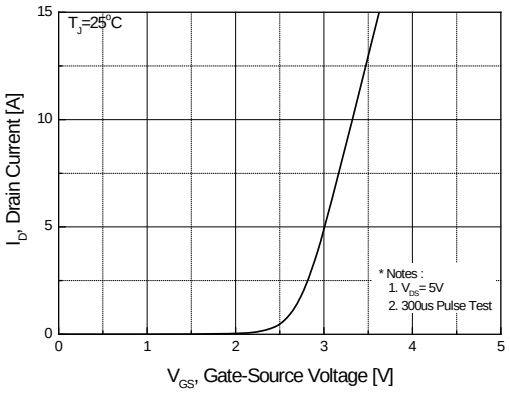


Figure 2. Transfer Characteristics

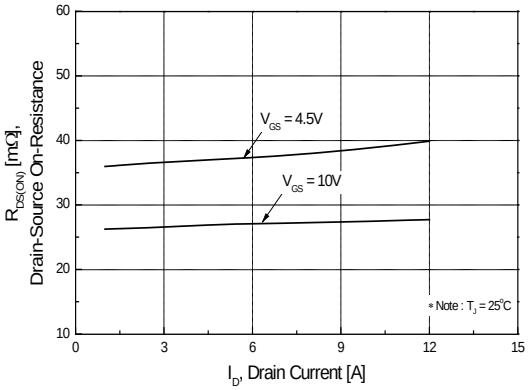


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

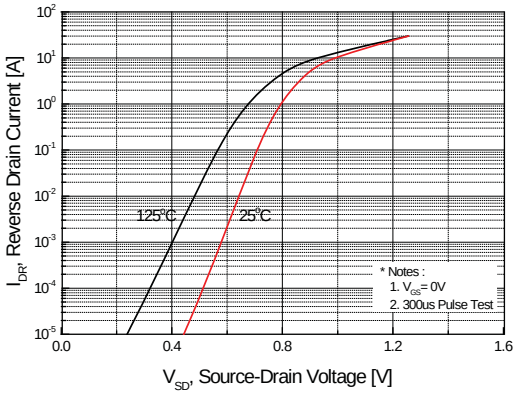


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

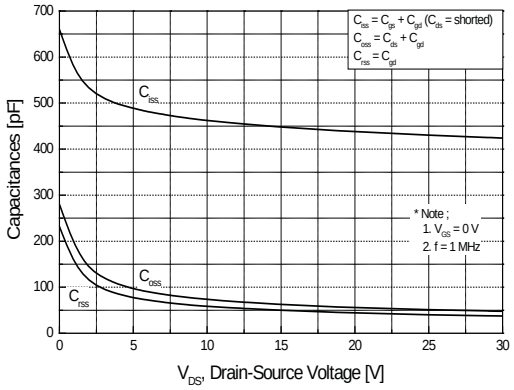


Figure 5. Capacitance Characteristics

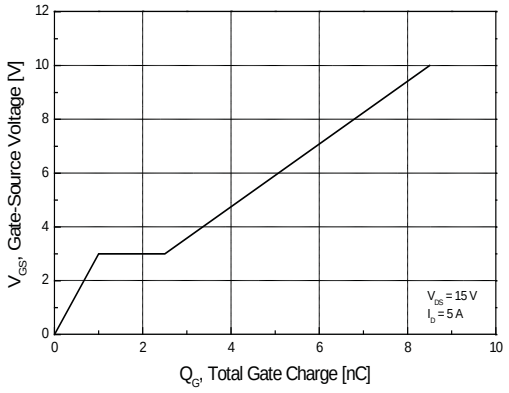


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

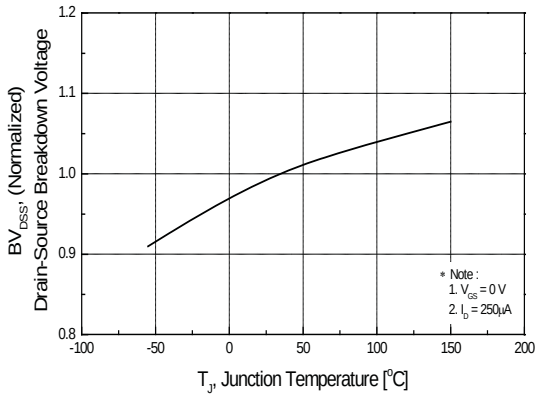


Figure 7. Breakdown Voltage Variation vs Temperature

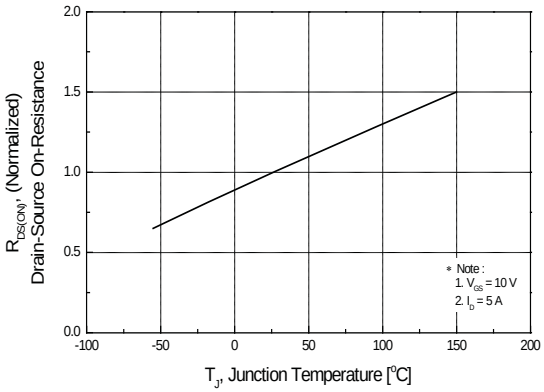


Figure 8. On-Resistance Variation vs Temperature

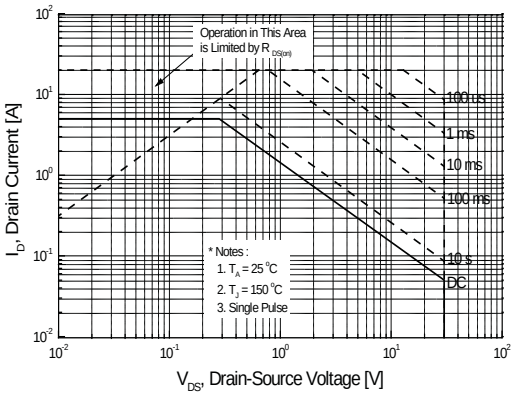


Figure 9. Maximum Safe Operating Area

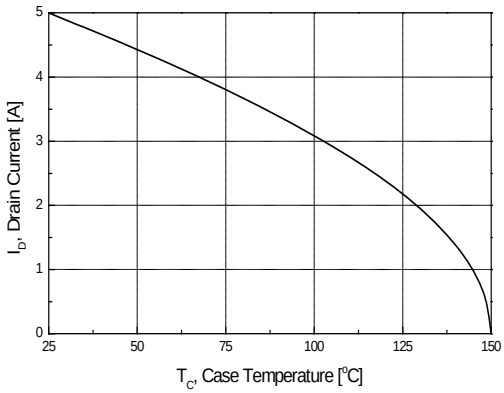


Figure 10. Maximum Drain Current vs Case Temperature

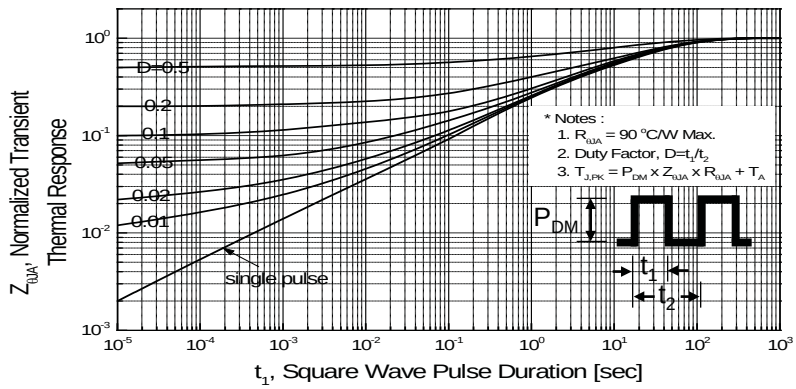


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

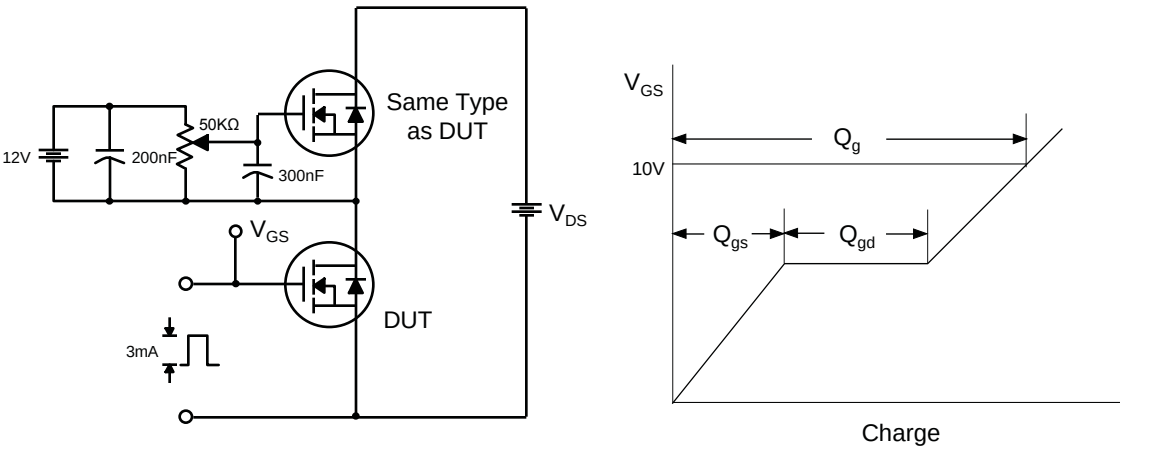


Fig 13. Resistive Switching Test Circuit & Waveforms

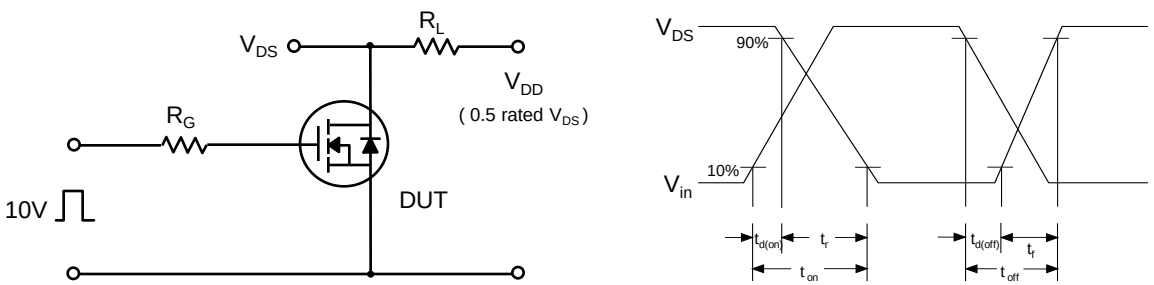


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

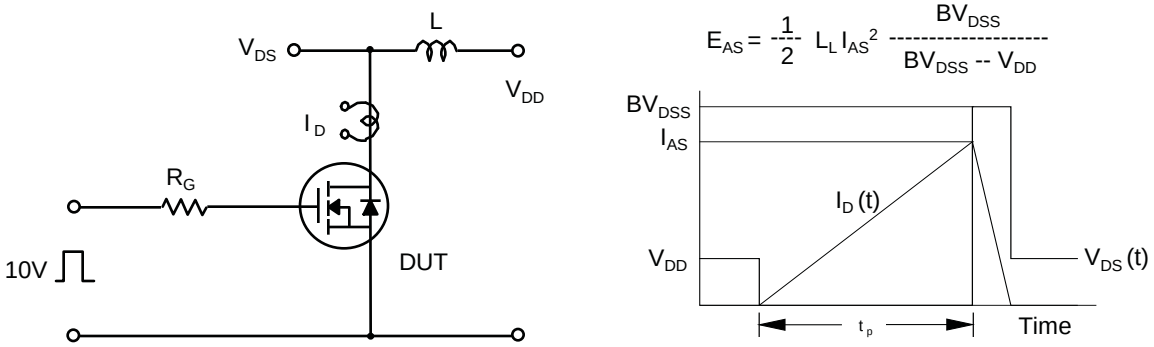
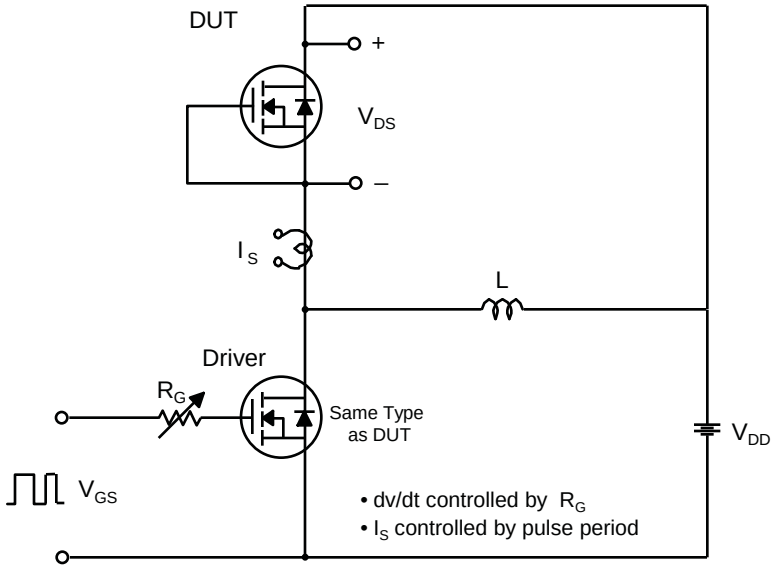
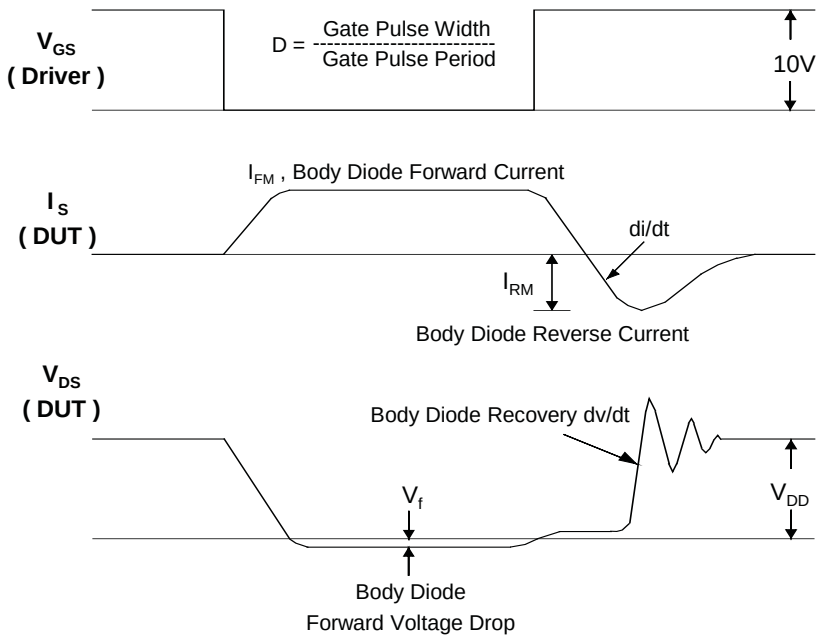


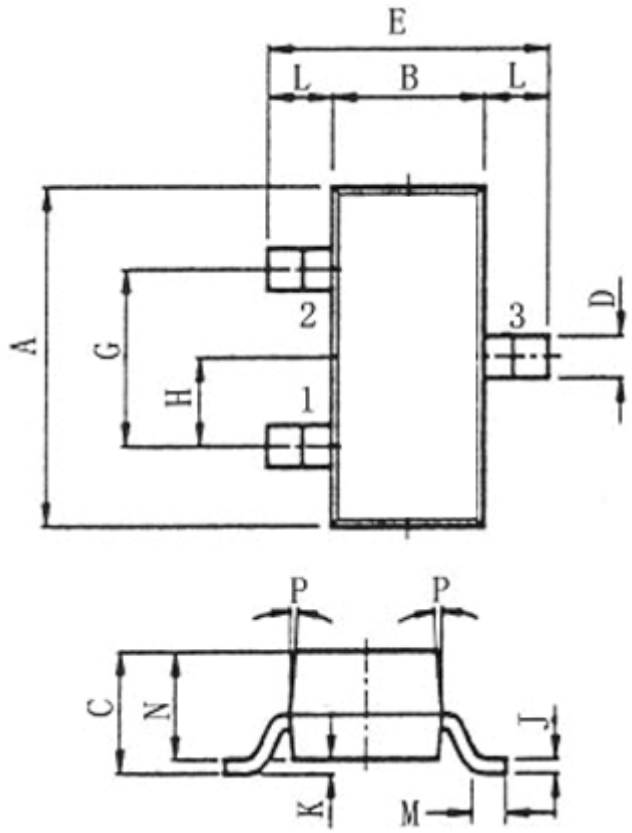
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimension & Marking Information

SOT-23



A	2.90±0.20
B	1.30+0.20/−0.15
C	1.30MAX
D	0.40+0.15/−0.05
E	2.40+0.30/−0.20
G	1.90±0.2
H	0.95±0.1
J	0.10+0.10/−0.05
K	0.00~0.10
L	0.55±0.1
M	0.20MIN
N	1.00+0.20/−0.10
P	7°